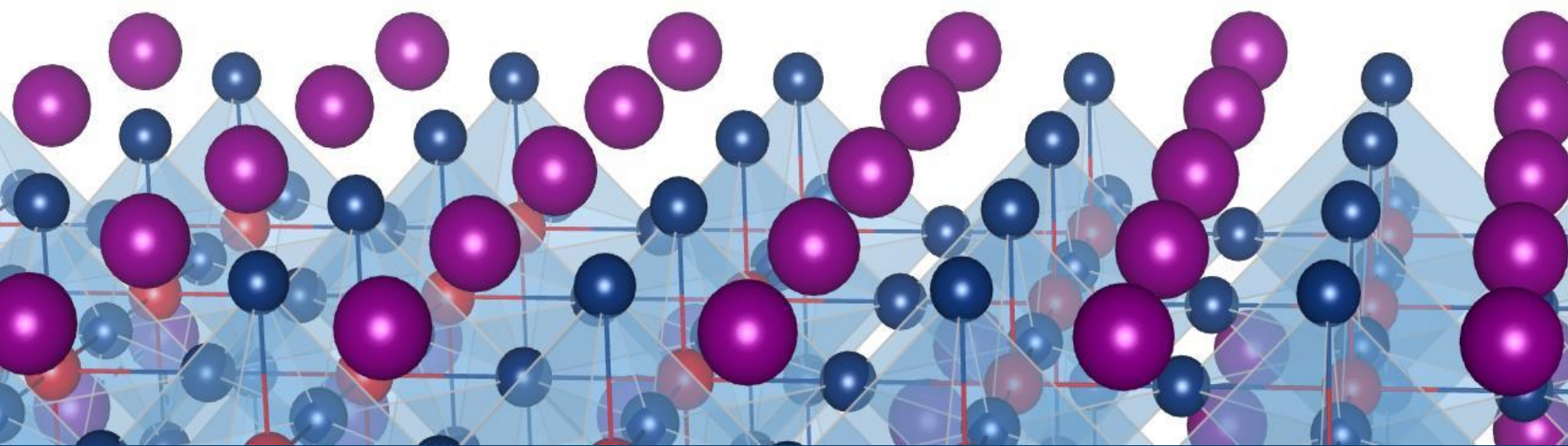


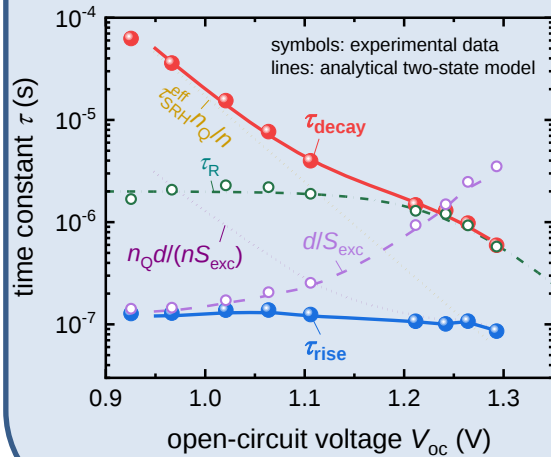


USING TRANSIENT METHODS TO CHARACTERIZE RECOMBINATION AND EXTRACTION IN HALIDE PEROVSKITE SOLAR CELLS

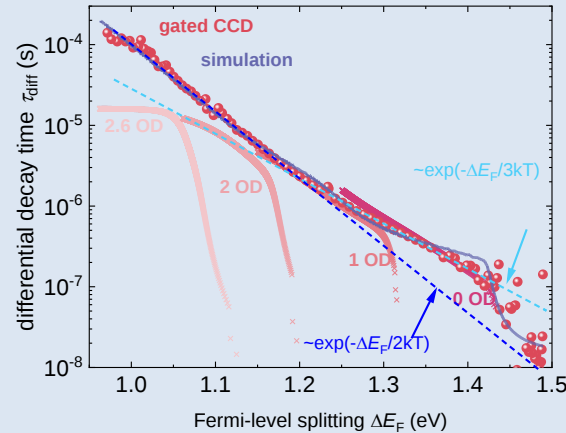
Thomas Kirchartz, Genghua Yan, Ye Yuan, Lisa Krückemeier, Uwe Rau

IEK-5 Photovoltaik, Forschungszentrum Jülich

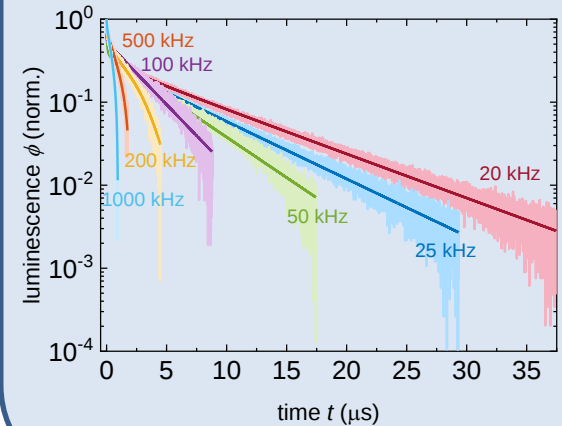
1) Charge separation vs. recombination

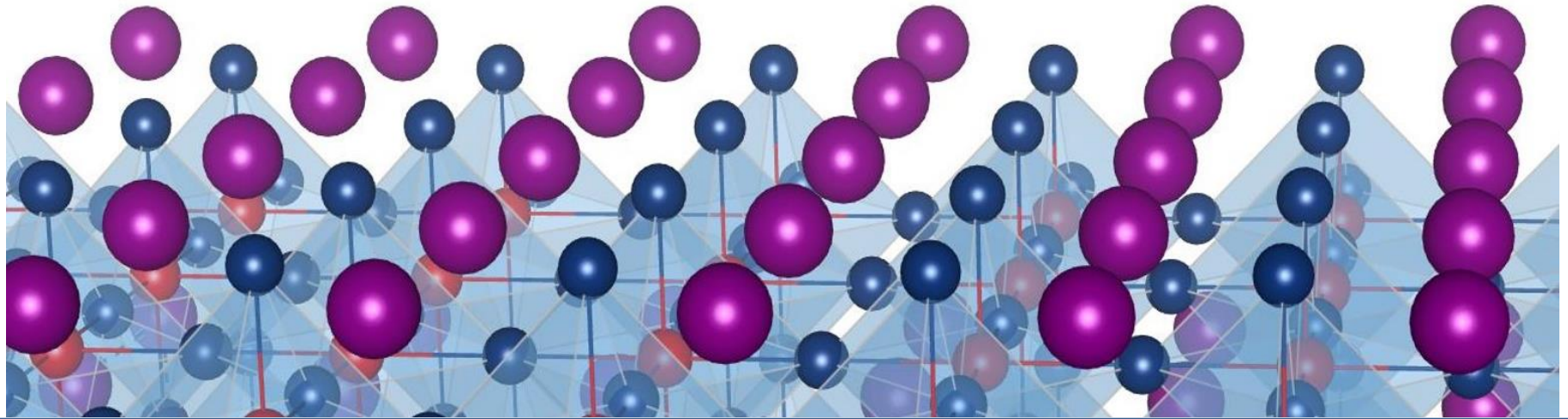


2) On the importance of shallow defects



3) On the importance of repetition rates



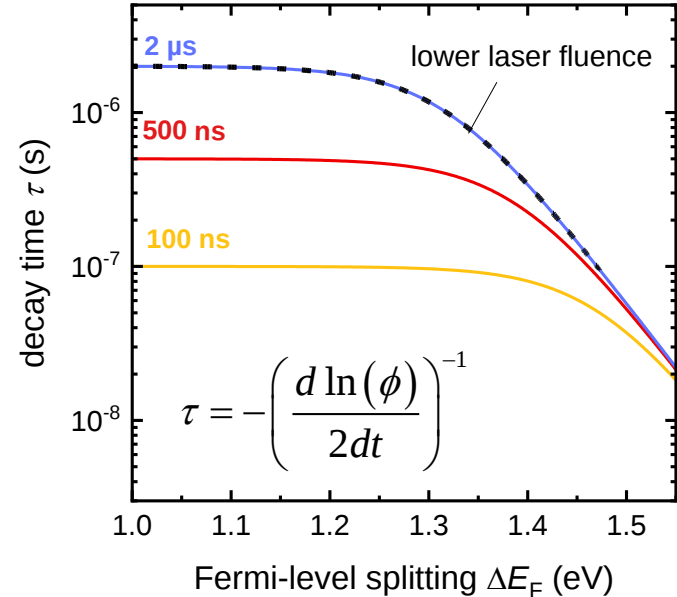
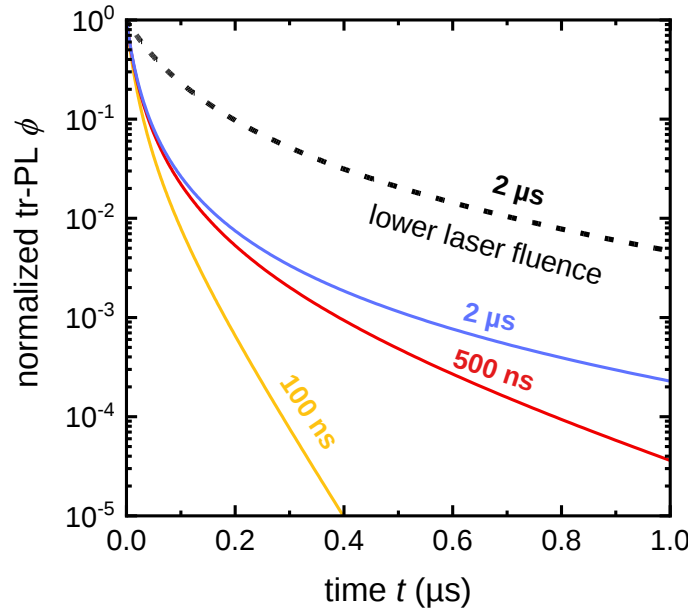
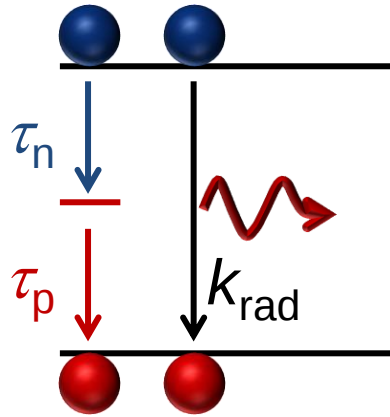
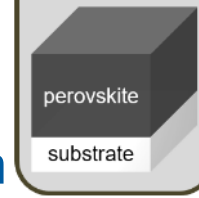


PART 0: INTRODUCTION

TRANSIENT PHOTOLUMINESCENCE AND LIFETIMES

Transient Photoluminescence

Layer on Glass – Bulk Recombination



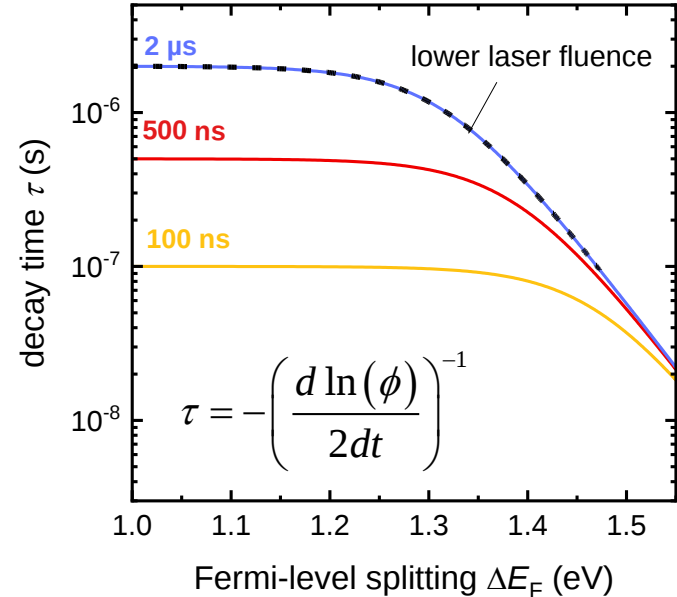
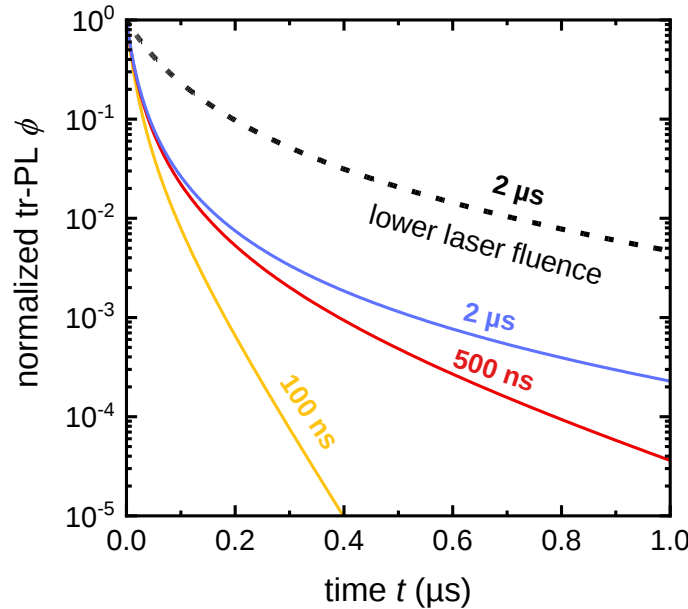
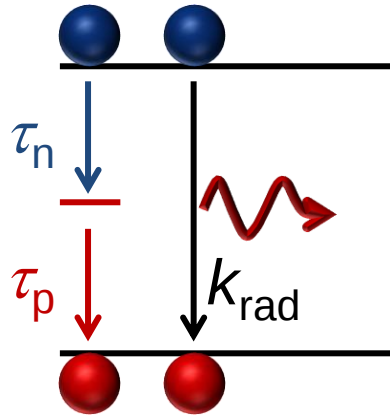
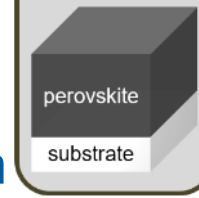
$$\frac{dn}{dt} = -k_{\text{rad}} n^2 - \frac{n}{\tau_p + \tau_n}$$

SRH + radiative recombination

← time

Transient Photoluminescence

Layer on Glass – Bulk Recombination

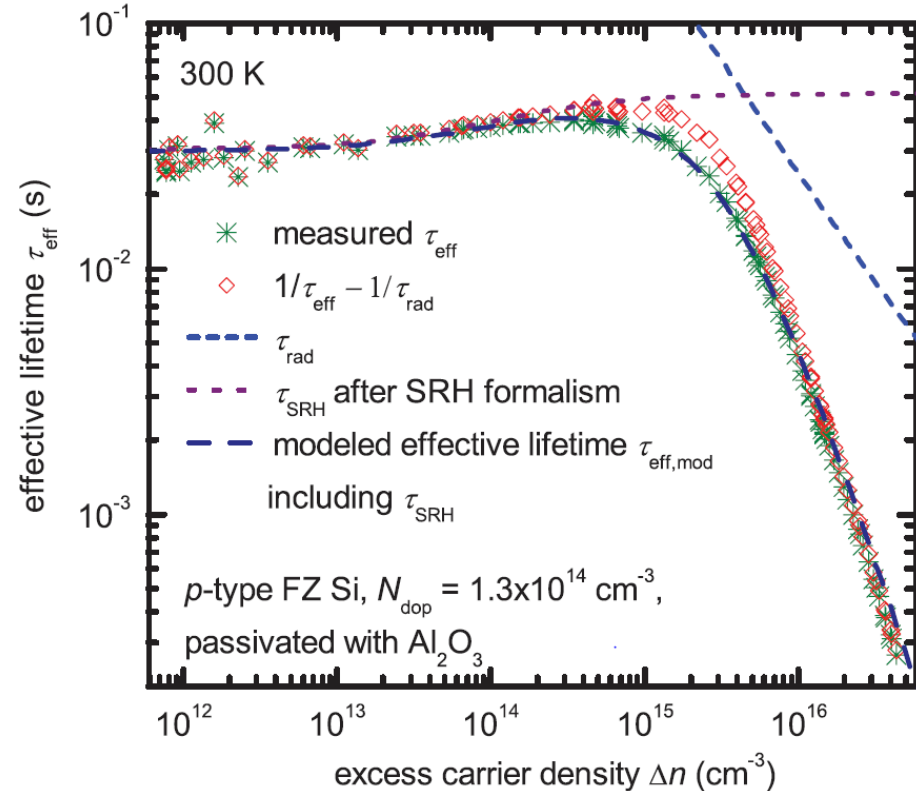
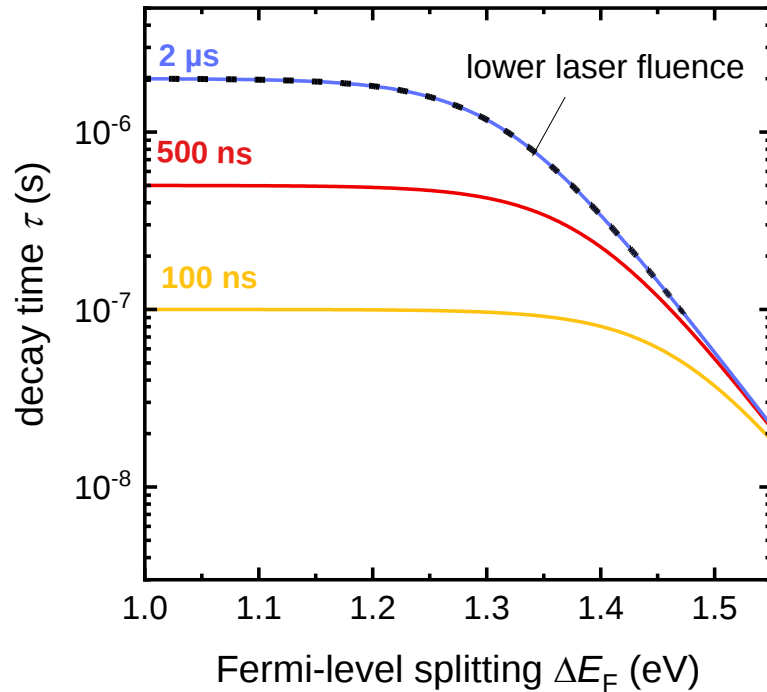


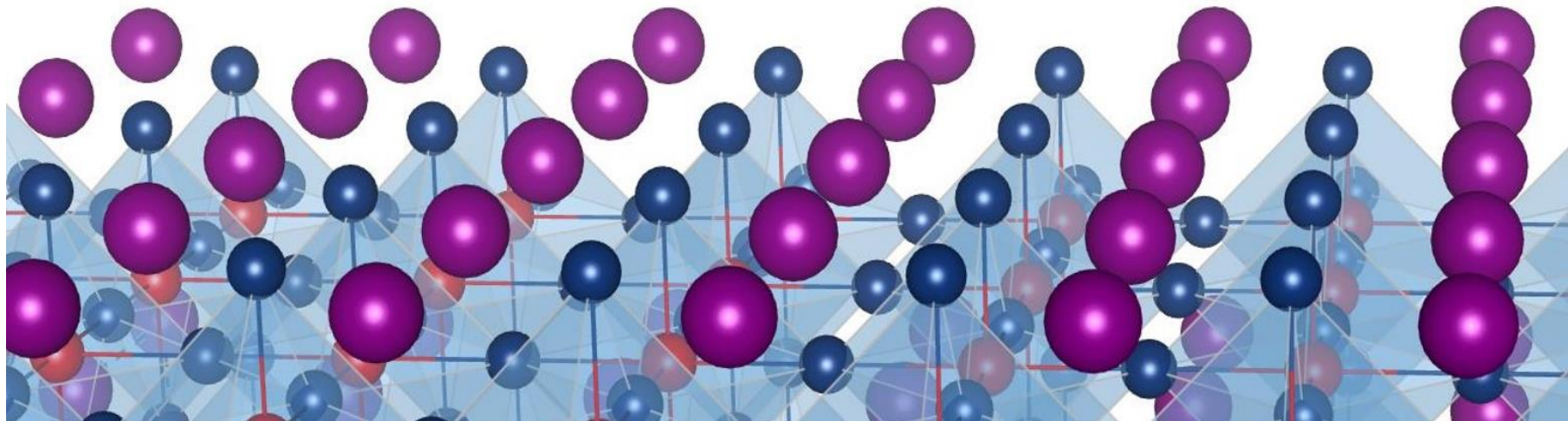
$$\tau_{\text{diff}} = -\frac{n}{dn/dt} = \frac{1}{k_{\text{rad}} n + \tau_p + \tau_n}$$

Decay Time

← time

Differential decay times in passivated Si wafers





PART 1: RECAP FROM HOPV 2022

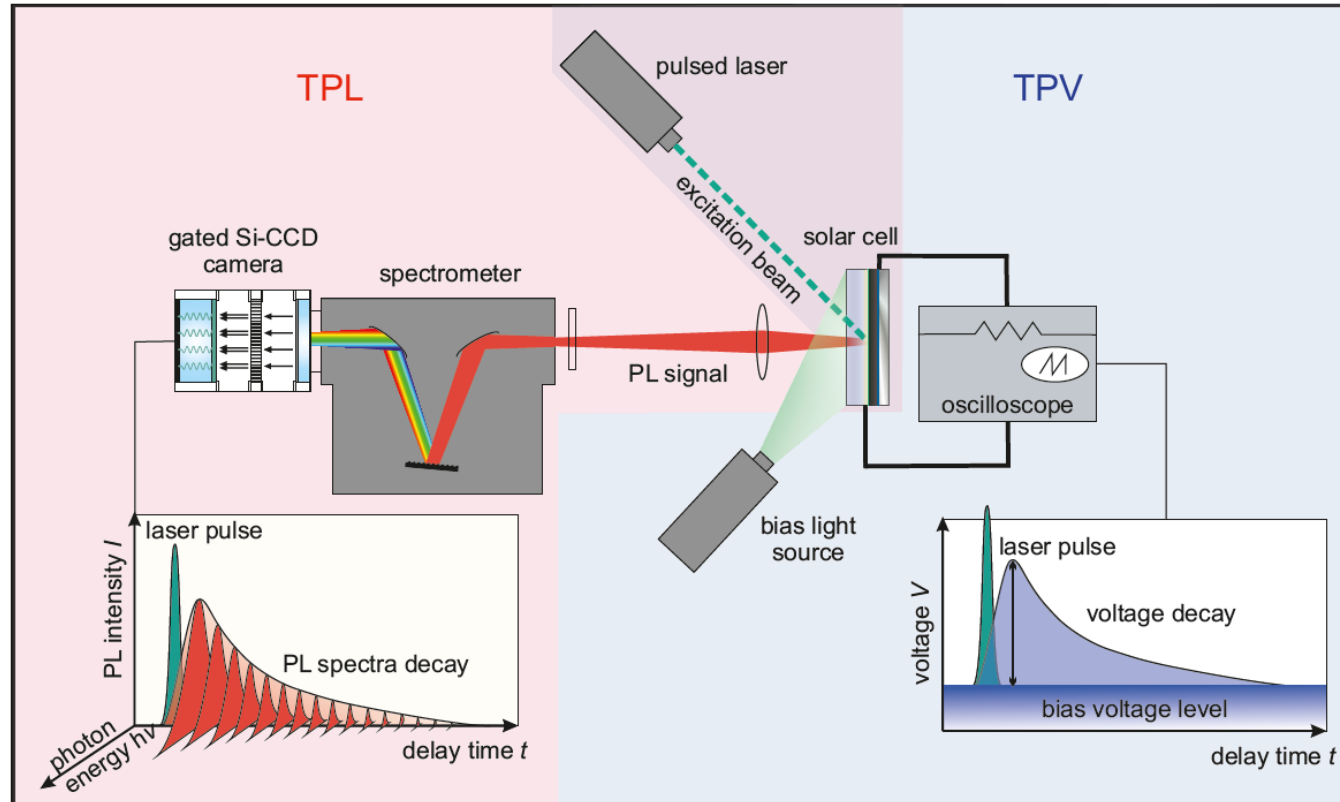
TRANSIENT PHOTOVOLTAGE VS. PHOTOLUMINESCENCE

Transient Photoluminescence (TPL)

measures the luminescence decay

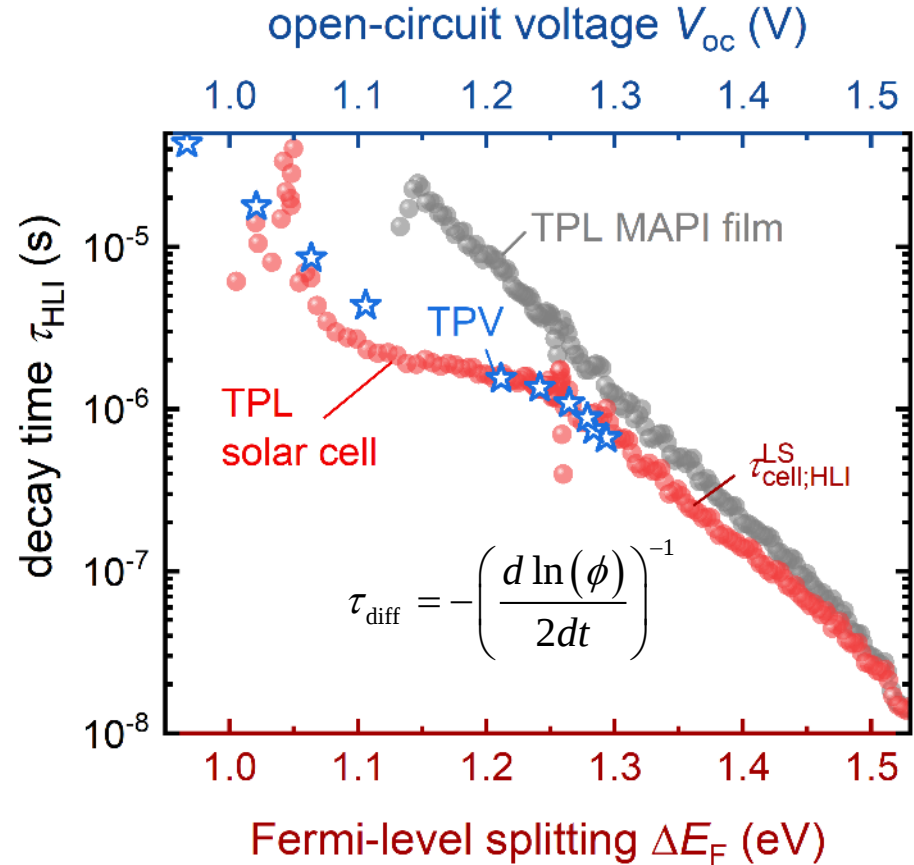
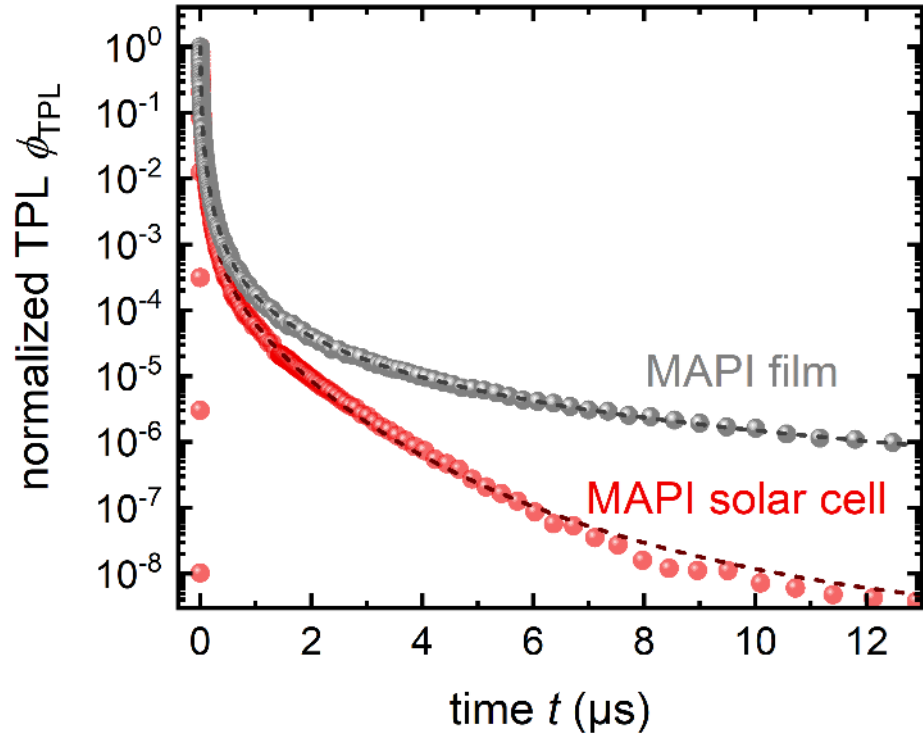
Transient Photovoltage (TPV)

measures the decay of an external voltage

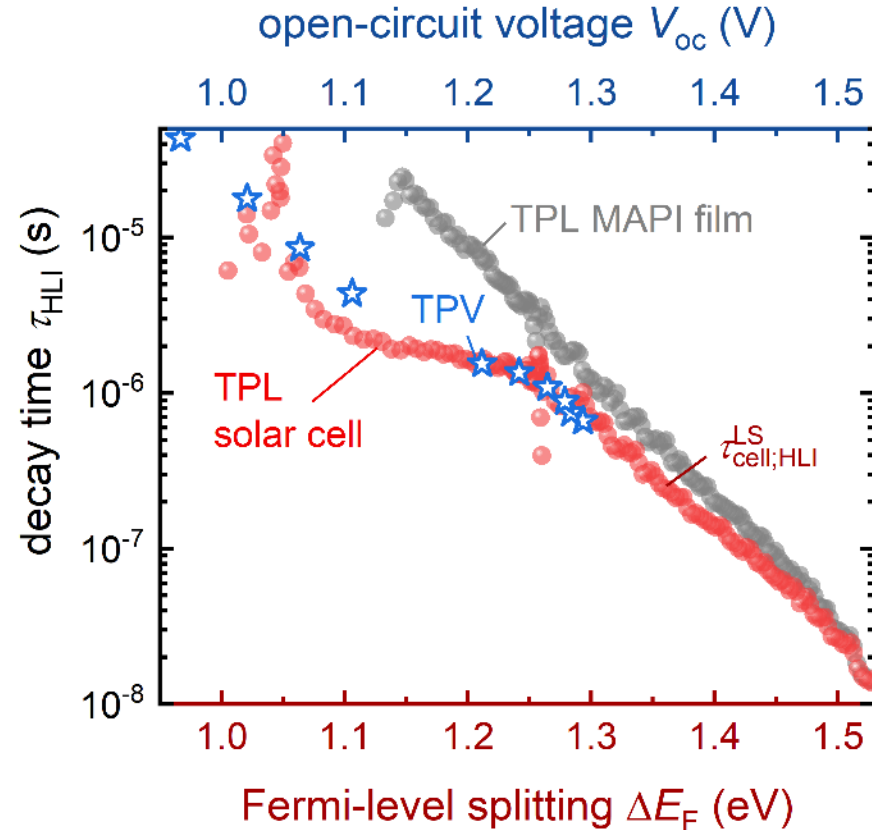


Transient Photoluminescence

Layer on Glass – Bulk Recombination



How to make sense out of it

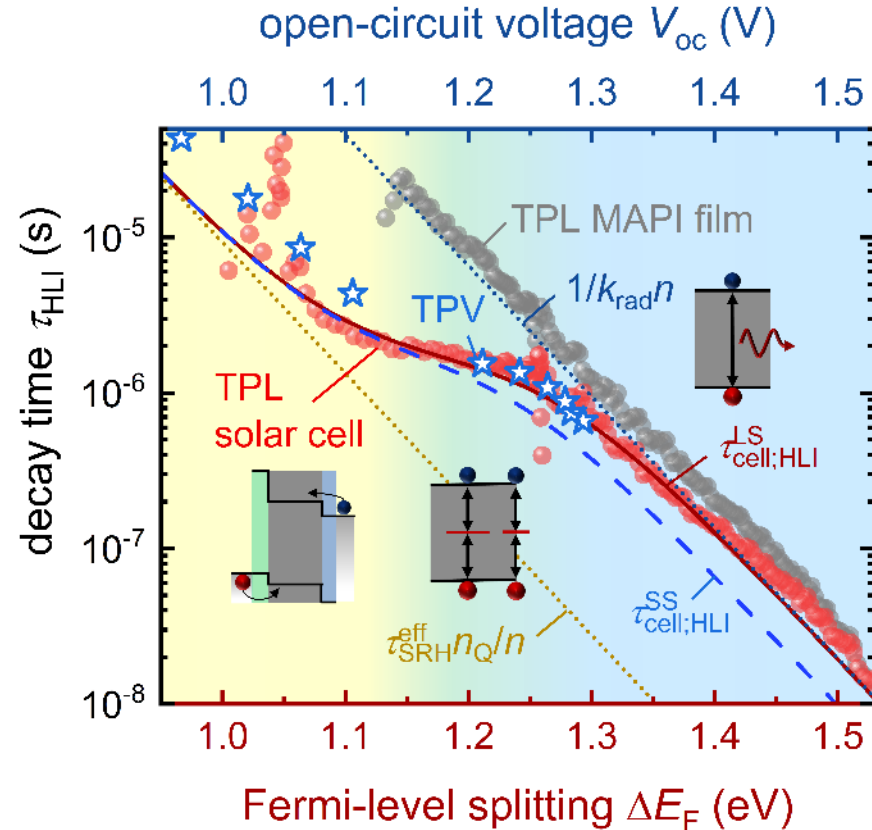


$$\frac{dn(t)}{dt} = -k_{rad}n(t)^2 - \frac{n(t)}{\tau_{SRH}^{bulk}} - \frac{C_{area}}{qd_{pero}} \frac{dV_{ext}(t)}{dt} + G$$

$$\tau_{cell,HLI}^{LS} = -\frac{n(t)}{dn(t)/dt} = \frac{n_Q/n(t)+1}{k_{rad}n(t)+1/\tau_{SRH}^{eff}}$$

$$n_Q = 2C_{area}k_BT/(q^2d_{pero})$$

How to make sense out of it

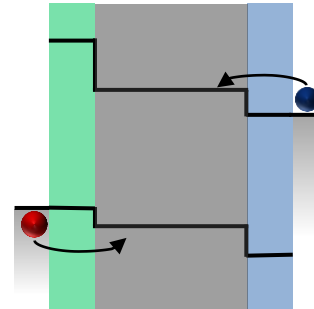


Capacitive discharging of the electrodes

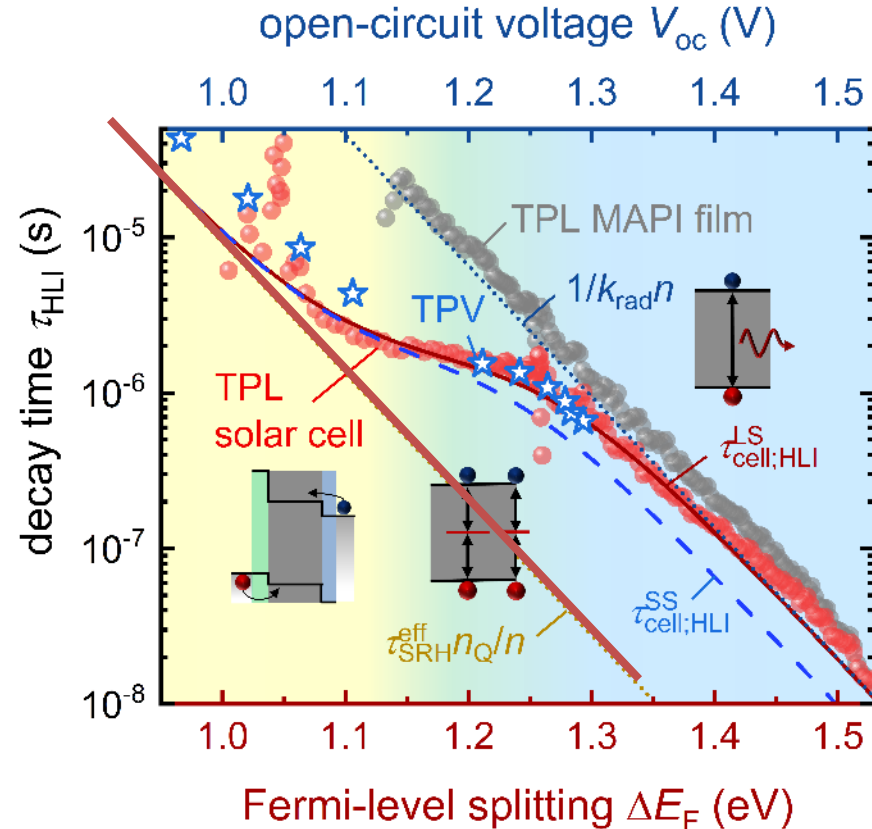
$$\frac{dn(t)}{dt} = -k_{rad}n(t)^2 - \frac{n(t)}{\tau_{SRH}^{bulk}} - \left[\frac{C_{area}}{qd_{pero}} \frac{dV_{ext}(t)}{dt} \right] + G$$

$$\tau_{cell,HLI}^{LS} = -\frac{n(t)}{dn(t)/dt} = \frac{n_Q/n(t)+1}{k_{rad}n(t)+1/\tau_{SRH}^{eff}}$$

$$n_Q = 2C_{area}k_B T / (q^2 d_{pero})$$



How to make sense out of it

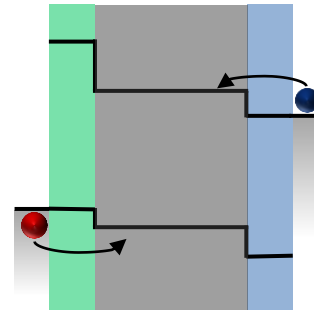


Capacitive discharging of the electrodes

$$\frac{dn(t)}{dt} = -k_{rad}n(t)^2 - \frac{n(t)}{\tau_{SRH}^{bulk}} - \left[\frac{C_{area}}{qd_{pero}} \frac{dV_{ext}(t)}{dt} \right] + G$$

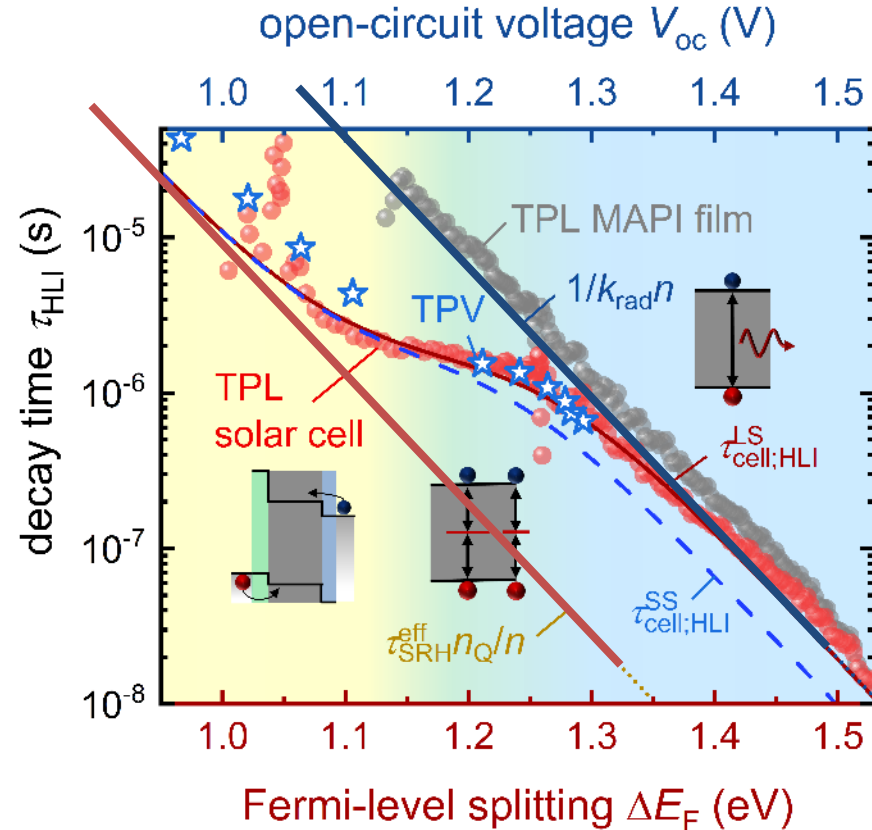
$$\tau_{cell,HLI}^{LS} = -\frac{n(t)}{dn(t)/dt} = \frac{n_Q/n(t)+1}{k_{rad}n(t)+1/\tau_{SRH}^{eff}}$$

$$n_Q = 2C_{area}k_B T / (q^2 d_{pero})$$



Re-injection of carriers into the perovskite layer

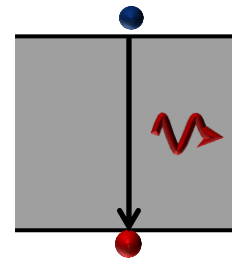
How to make sense out of it



$$\frac{dn(t)}{dt} = -k_{rad}n(t)^2 - \frac{n(t)}{\tau_{SRH}^{bulk}} - \frac{C_{area}}{qd_{pero}} \frac{dV_{ext}(t)}{dt} + G$$

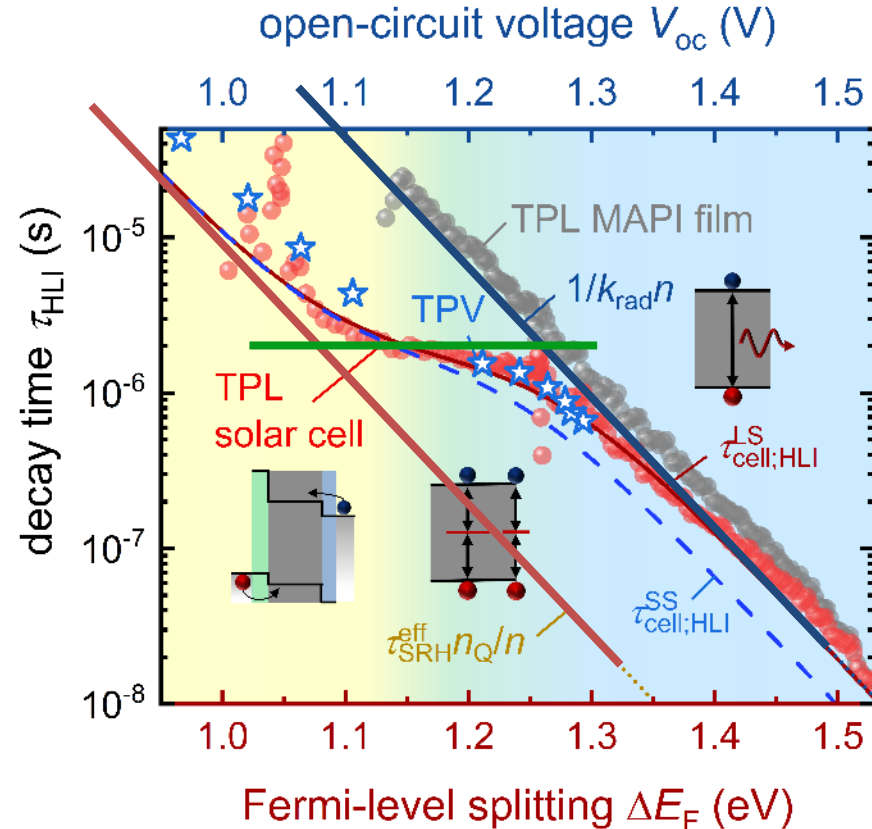
$$\tau_{cell,HLI}^{LS} = -\frac{n(t)}{dn(t)/dt} = \frac{n_Q/n(t)+1}{k_{rad}n(t)+1/\tau_{SRH}^{eff}}$$

$$n_Q = 2C_{area}k_B T / (q^2 d_{pero})$$



Radiative
recombination

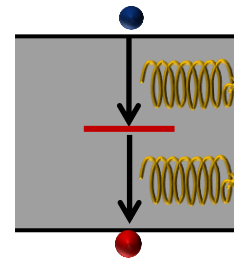
How to make sense out of it



$$\frac{dn(t)}{dt} = -k_{rad}n(t)^2 - \frac{n(t)}{\tau_{SRH}^{bulk}} - \frac{C_{area}}{qd_{pero}} \frac{dV_{ext}(t)}{dt} + G$$

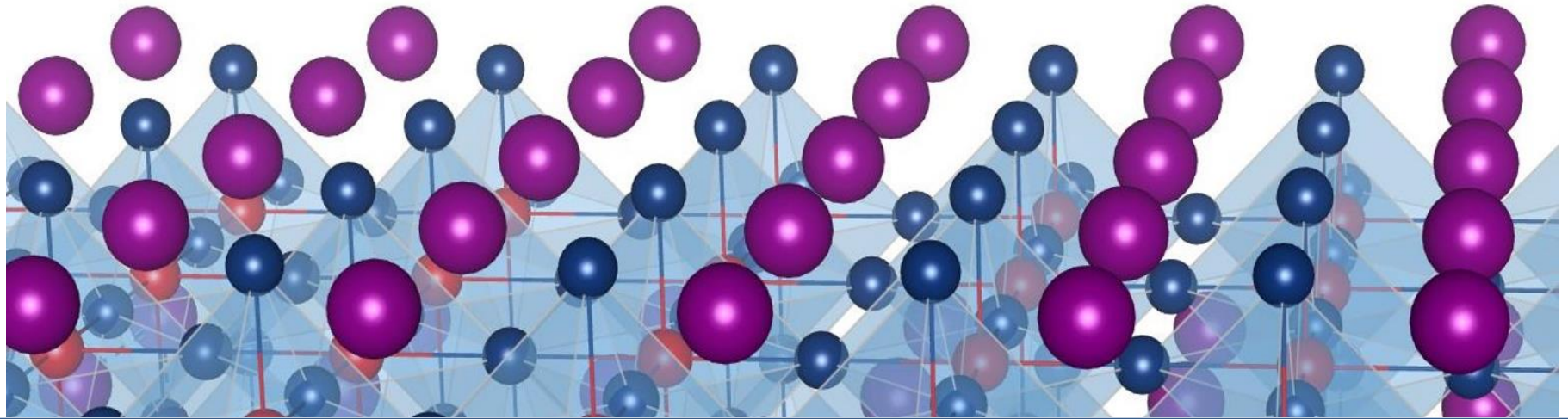
$$\tau_{cell,HLI}^{LS} = -\frac{n(t)}{dn(t)/dt} = \frac{n_Q/n(t)+1}{k_{rad}n(t)+1/\tau_{SRH}^{eff}}$$

$$n_Q = 2C_{area}k_B T / (q^2 d_{pero})$$



Shockley-Read-
Hall recombination

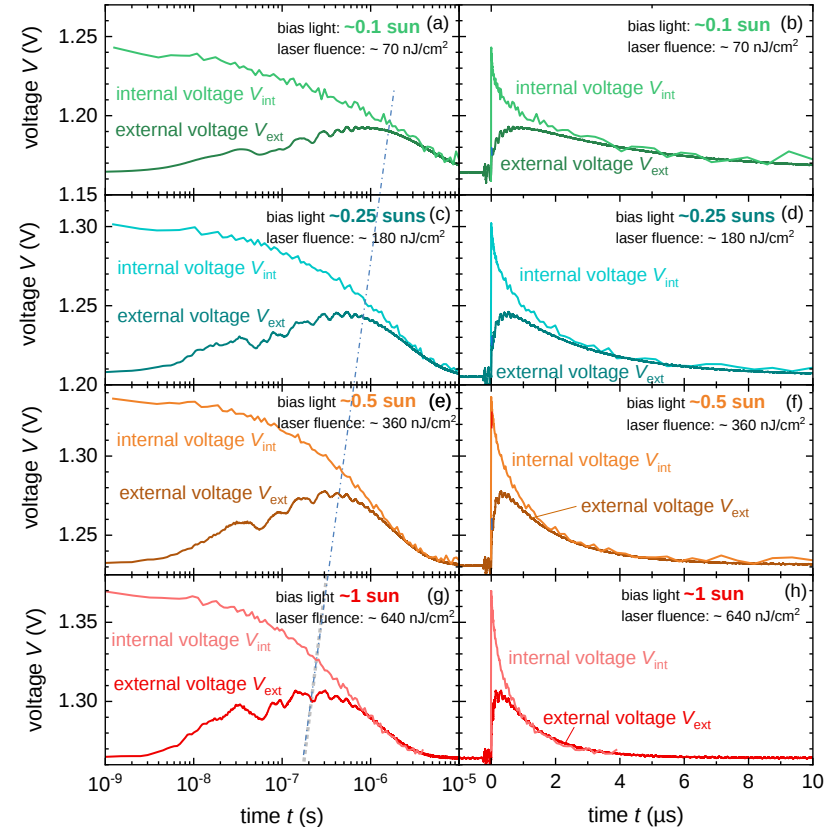
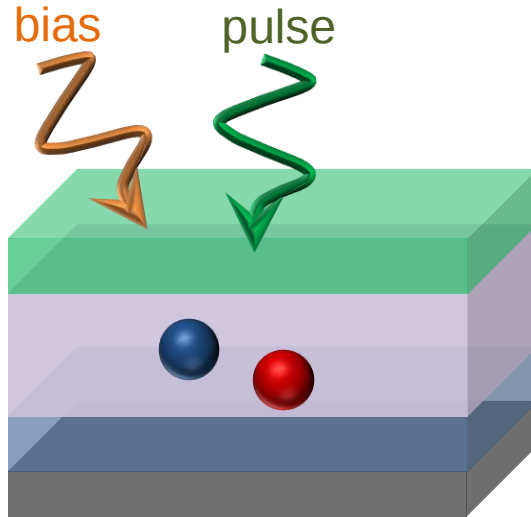
Krückemeier et al. Adv. Energy Mat. 2021, 11, 2102290



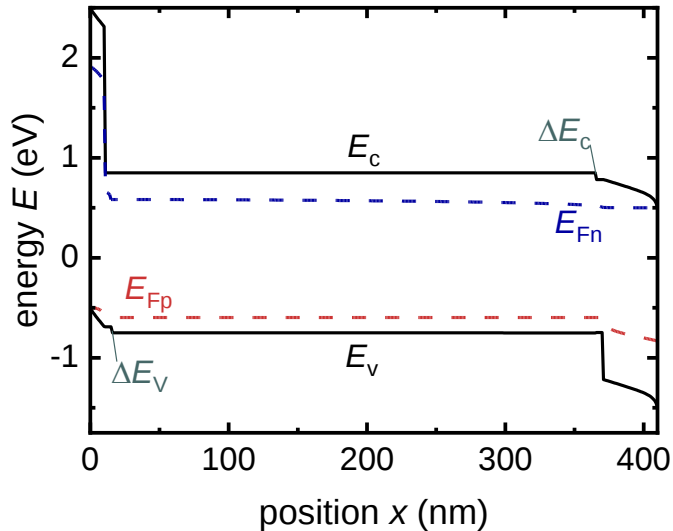
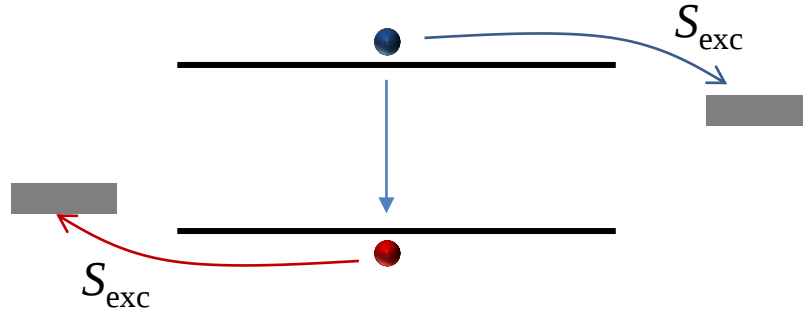
PART 2: ANALYSIS OF SMALL SIGNAL MEASUREMENTS

RECOMBINATION VS. EXTRACTION

Experimental data – internal vs. external voltage



Transient Methods – Recombination and Extraction



$$\frac{dn}{dt} = -k_{\text{rad}} n^2 - \frac{n}{\tau_{\text{SRH}}^{\text{eff}}} - \frac{S_{\text{exc}}}{d} \left(n - n_i \exp\left(\frac{qV_{\text{ext}}}{2kT}\right) \right) + G$$

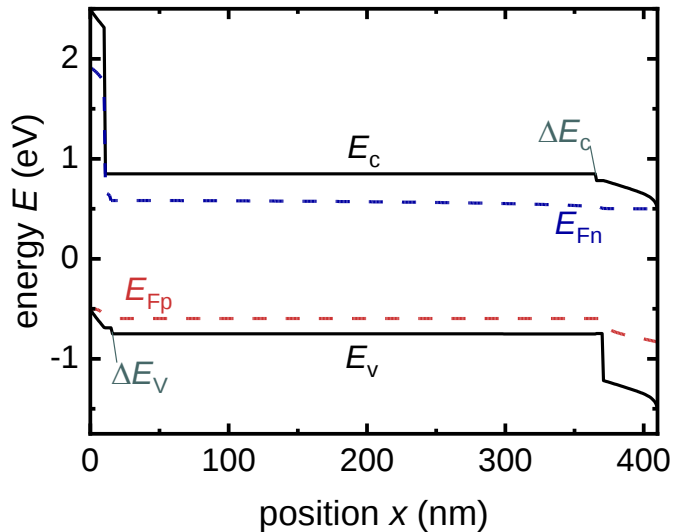
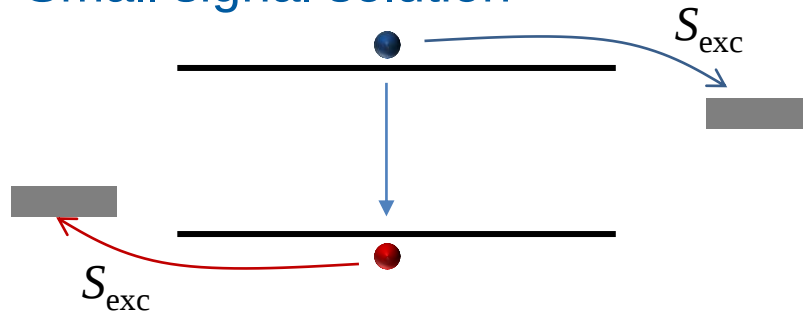
Recombination and extraction

$$\frac{dV_{\text{ext}}}{dt} = \frac{qS_{\text{exc}}}{C_{\text{area}}} \left(n - n_i \exp\left(\frac{qV_{\text{ext}}}{2kT}\right) \right)$$

Electrode (dis)charging

Recombination and Extraction

Small signal solution



$$\frac{d}{dt} \begin{pmatrix} \delta V_{\text{int}} \\ \delta V_{\text{ext}} \end{pmatrix} = \begin{pmatrix} -\left(\frac{1}{\tau_{\text{SRH}}^{\text{eff}}} + 2k_{\text{rad}} n_{\text{bias}} + \frac{S_{\text{exc}}}{d} \right) & \frac{S_{\text{exc}}}{d} \\ \frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q} & -\frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q} \end{pmatrix} \begin{pmatrix} \delta V_{\text{int}} \\ \delta V_{\text{ext}} \end{pmatrix}$$

$$\tau_{\text{rise}} = \frac{2}{k_1 + k_2 + k_3 + \sqrt{(k_1 + k_2 + k_3)^2 - 4k_1 k_3}}$$

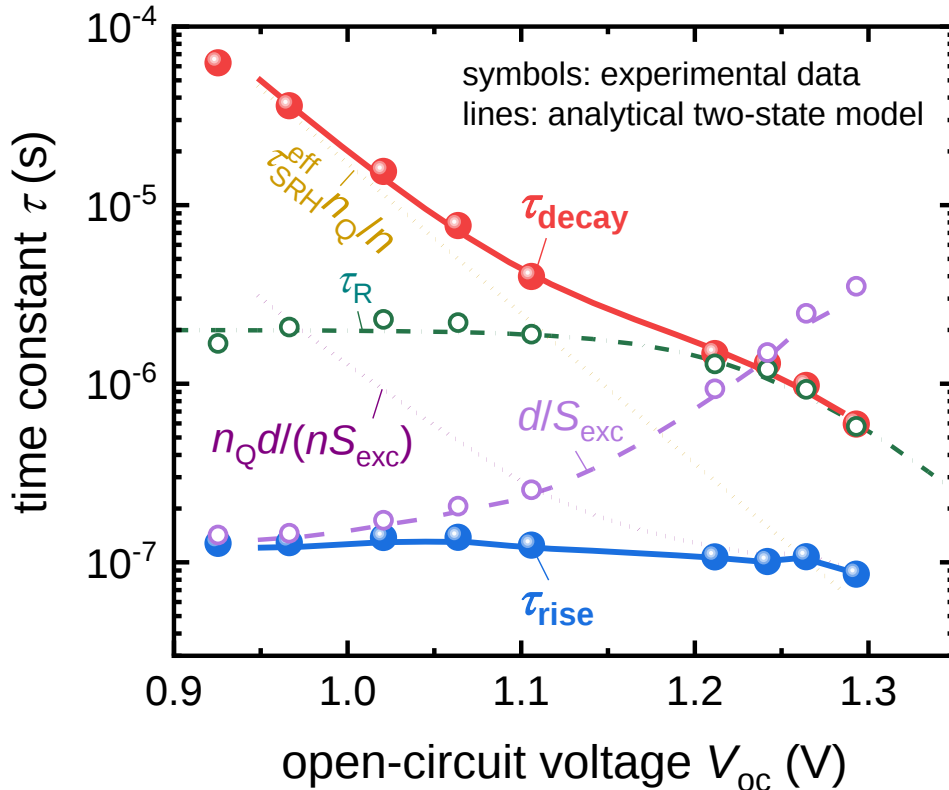
$$\tau_{\text{decay}} = \frac{2}{k_1 + k_2 + k_3 - \sqrt{(k_1 + k_2 + k_3)^2 - 4k_1 k_3}}$$

$$k_1 = \frac{1}{\tau_{\text{SRH}}^{\text{eff}}} + 2k_{\text{rad}} n_{\text{bias}}, \quad k_2 = \frac{S_{\text{exc}}}{d}, \quad k_3 = \frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q}$$

Inverse Eigenvalues of Matrix

Recombination and Extraction

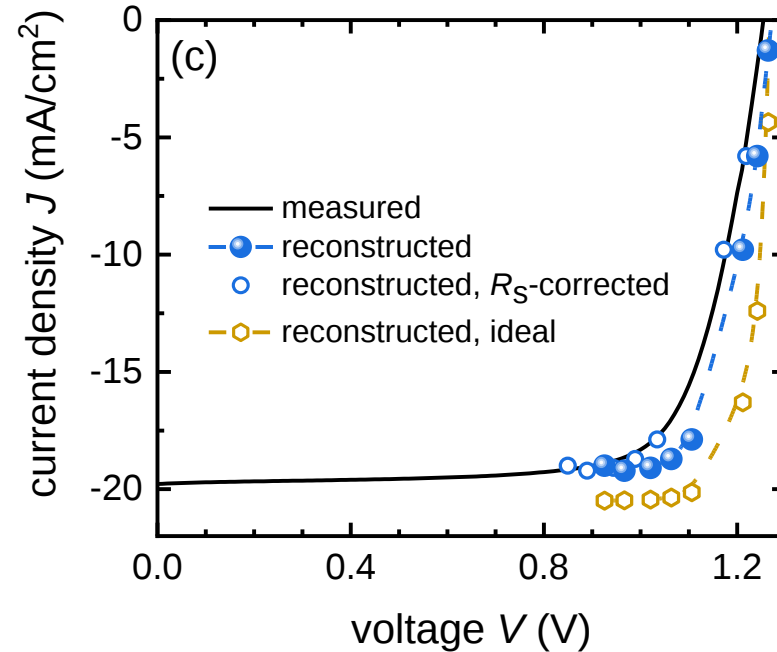
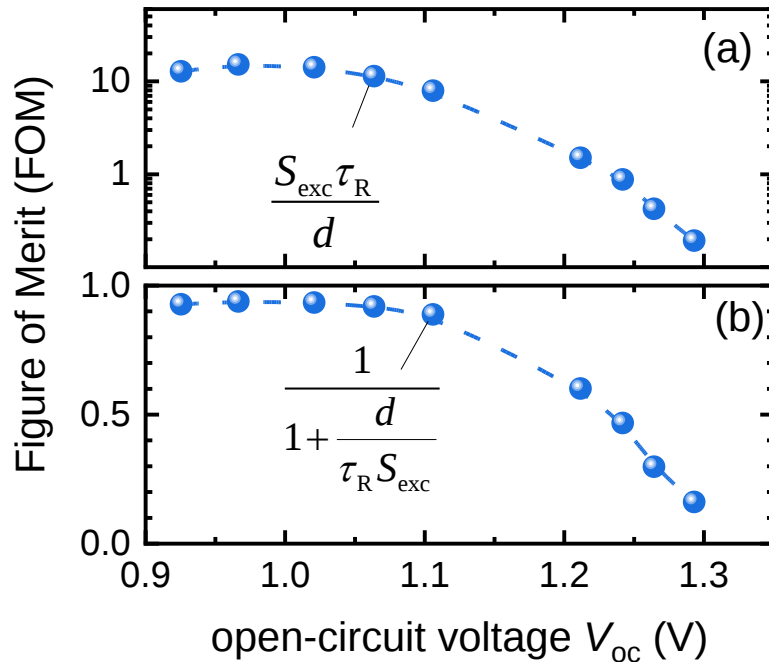
Comparison with Experiment



$$\tau_{\text{decay}} \approx \frac{dn_{\text{Q}}}{S_{\text{exc}} n_{\text{bias}}} + \frac{\tau_{\text{R}} n_{\text{Q}}}{n_{\text{bias}}} + \tau_{\text{R}}$$

$$\tau_{\text{rise}} \approx \left(\frac{1}{\tau_{\text{R}}} + \frac{S_{\text{exc}}}{d} + \frac{S_{\text{exc}} n_{\text{bias}}}{dn_{\text{Q}}} \right)^{-1}$$

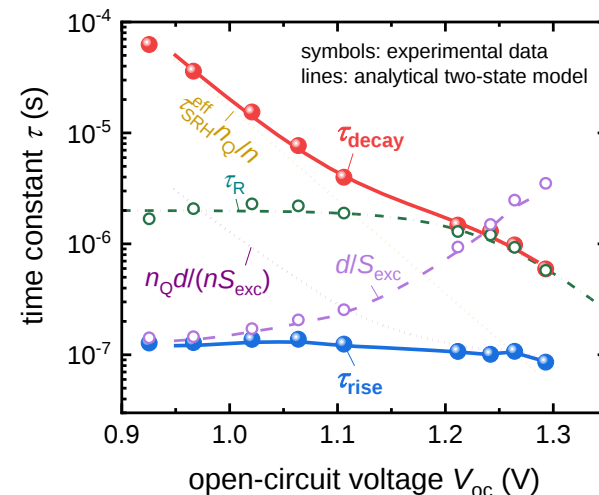
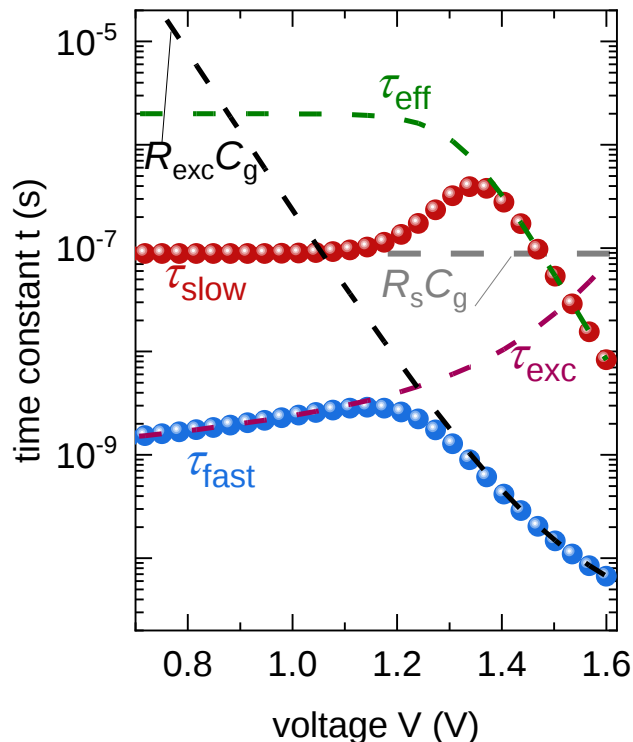
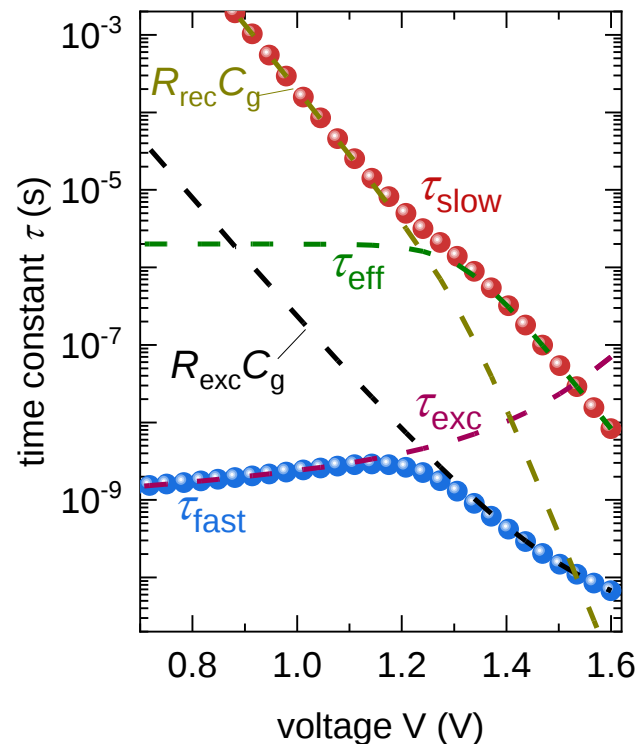
Collection Efficiencies and Impact on *JV* curves



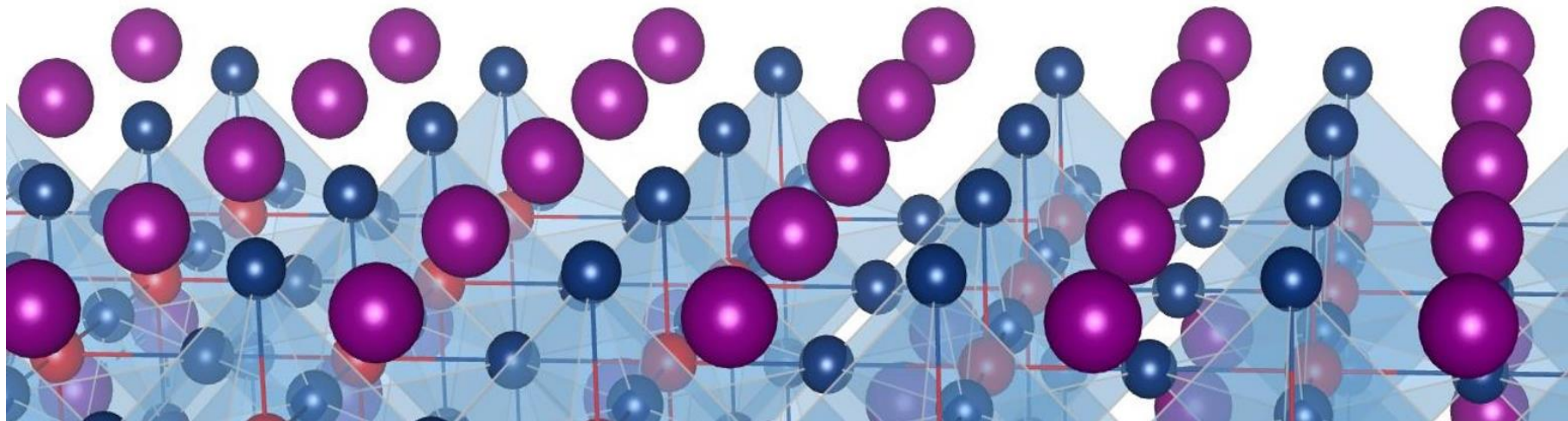
$$J = qd(R - G) = qd \left(\frac{1}{1 + d/(S_{\text{exc}} \tau_R)} \right) \left[\frac{n_0}{\tau_R} \exp \left(\frac{qV_{\text{ext}}}{2k_B T} \right) - G \right]$$

Frequency-Domain Methods

simulated data (freq. domain)



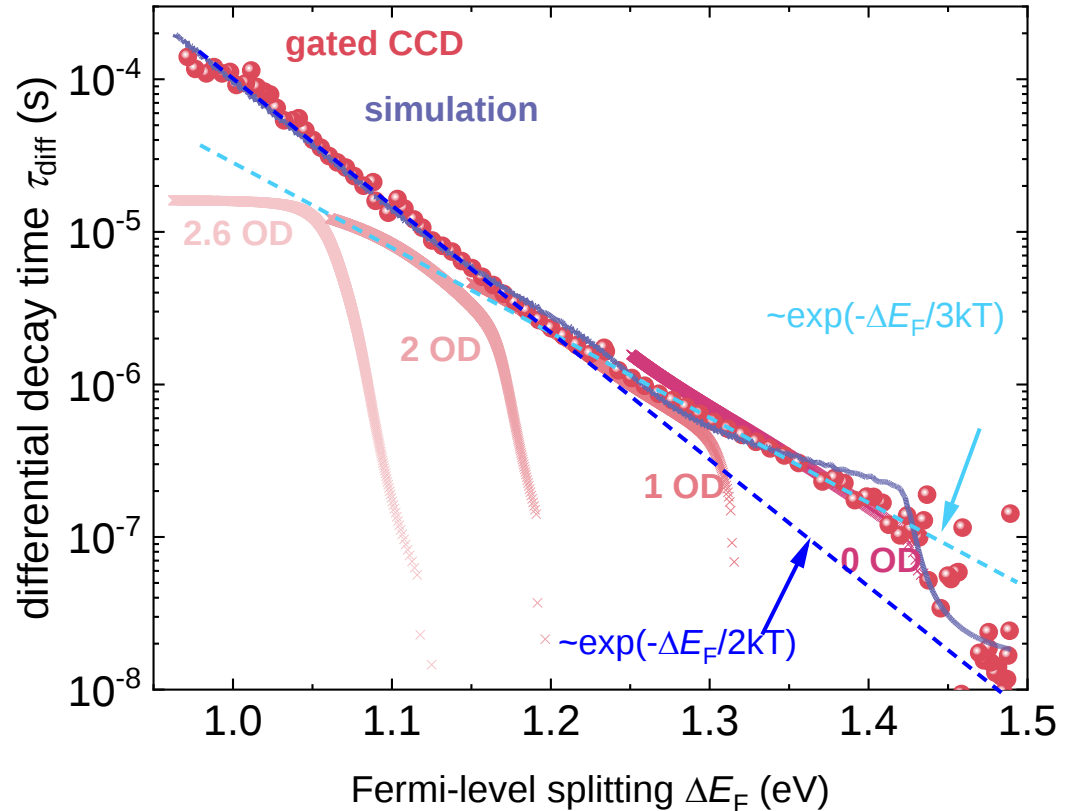
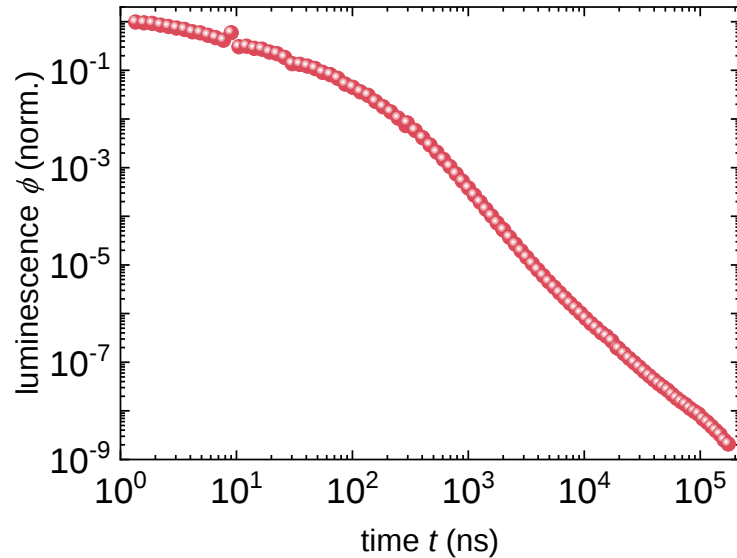
Experimental data
(time domain)



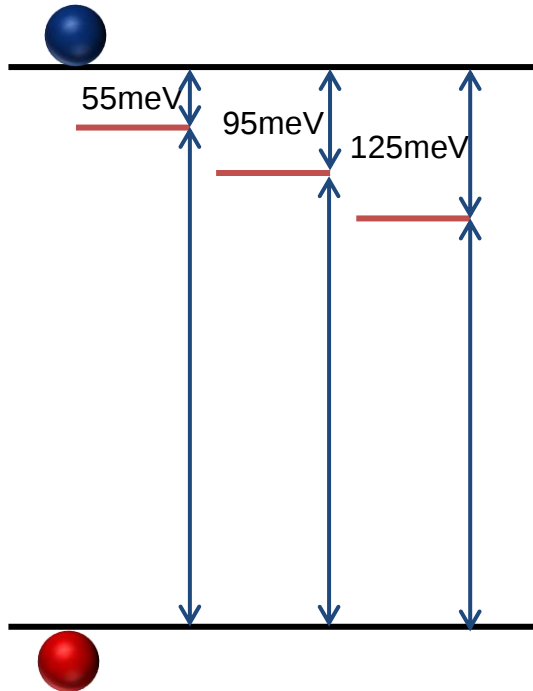
PART 3: SHALLOW DEFECTS

AND HOW THEY CHANGE THE SITUATION

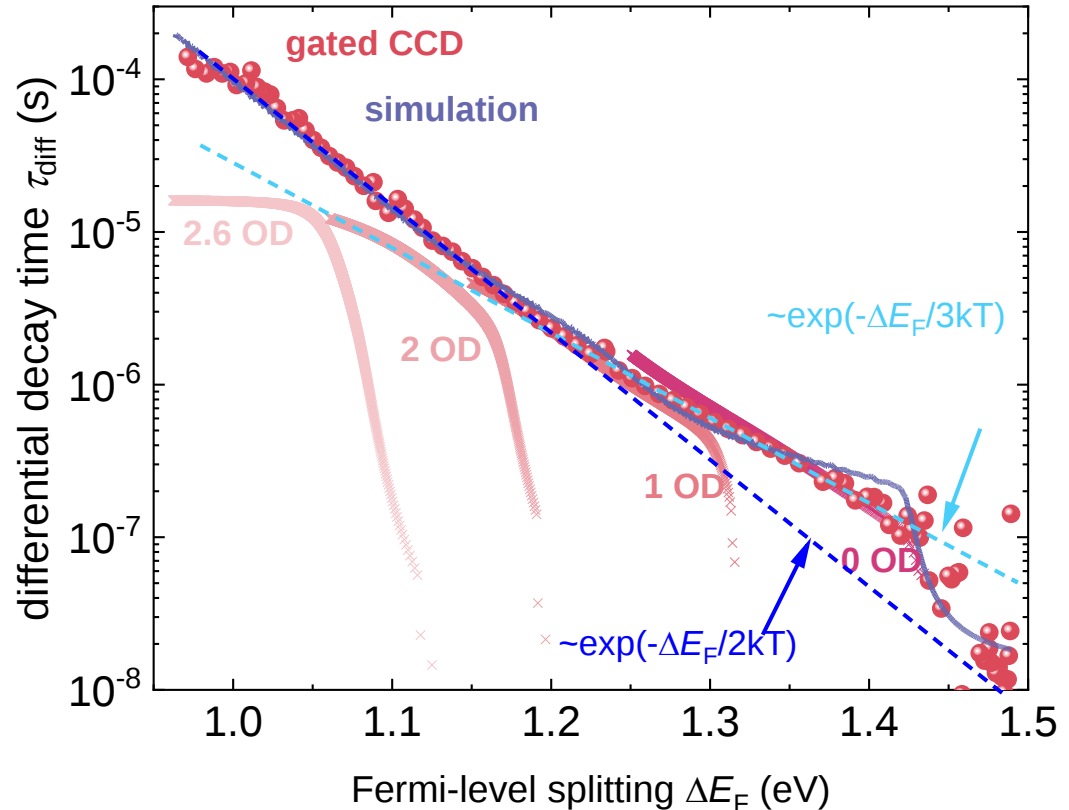
High dynamic range tr-PL



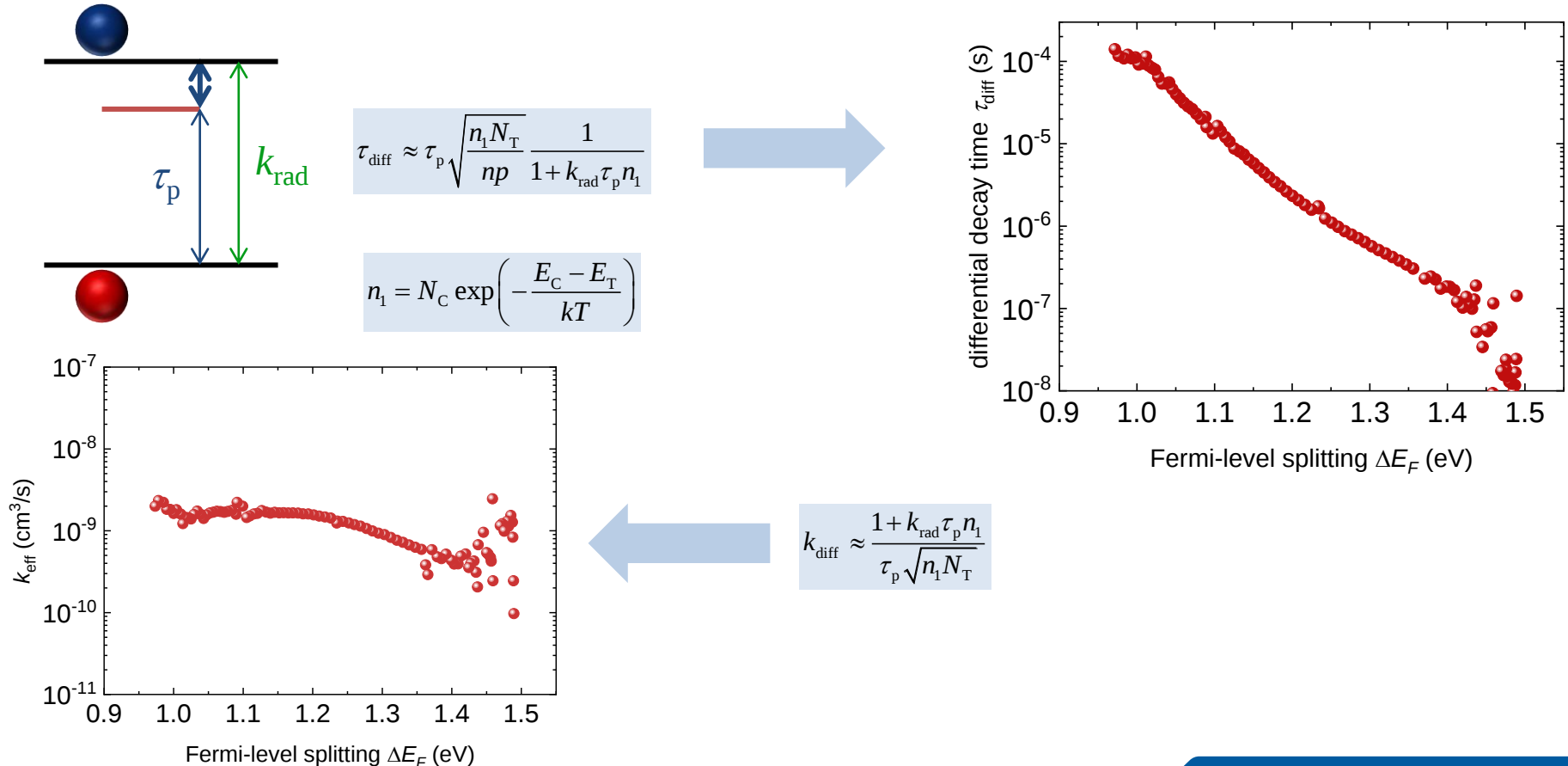
Defect levels assumed in the modelling

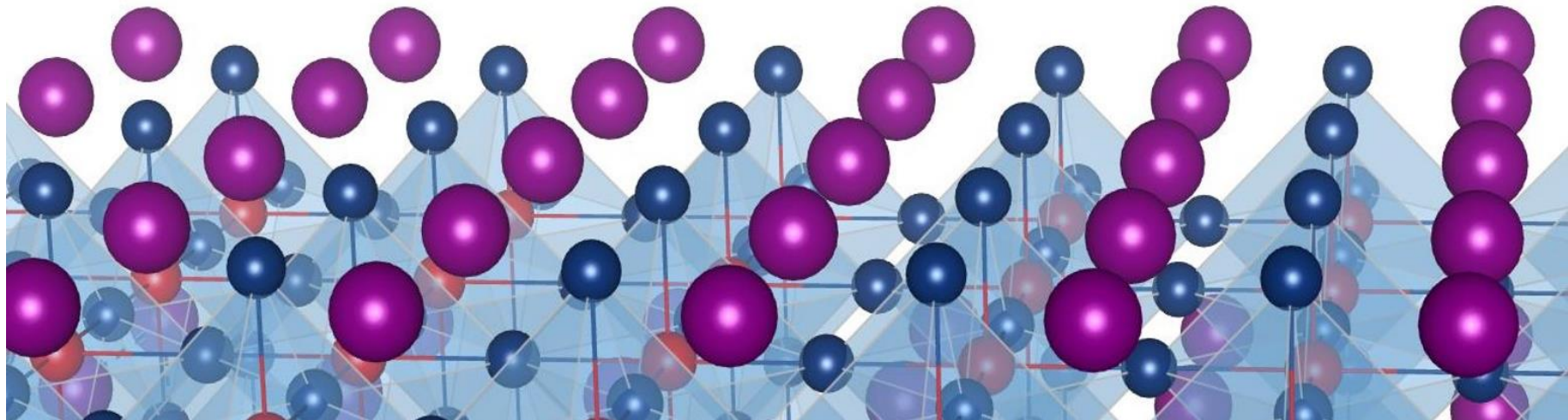


schematic not quite to scale



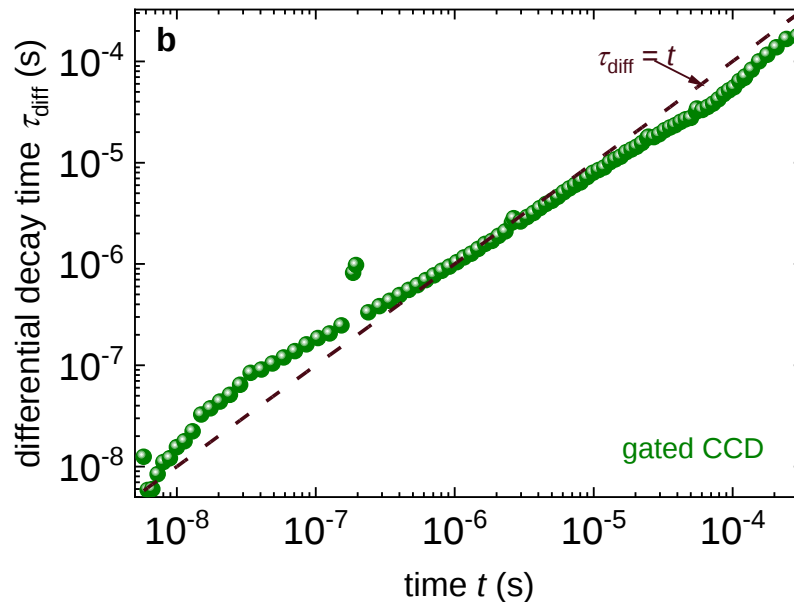
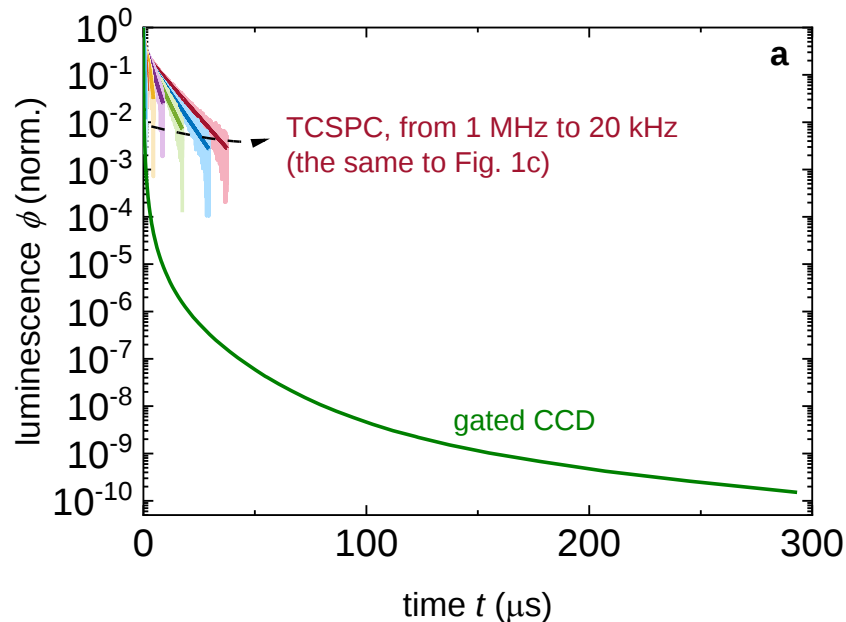
On the presence or absence of deep defects





PART 4: REPETITION RATES AND HOW THEY AFFECT DECAY TIMES

Why $\tau = t$ can be a decent approximation

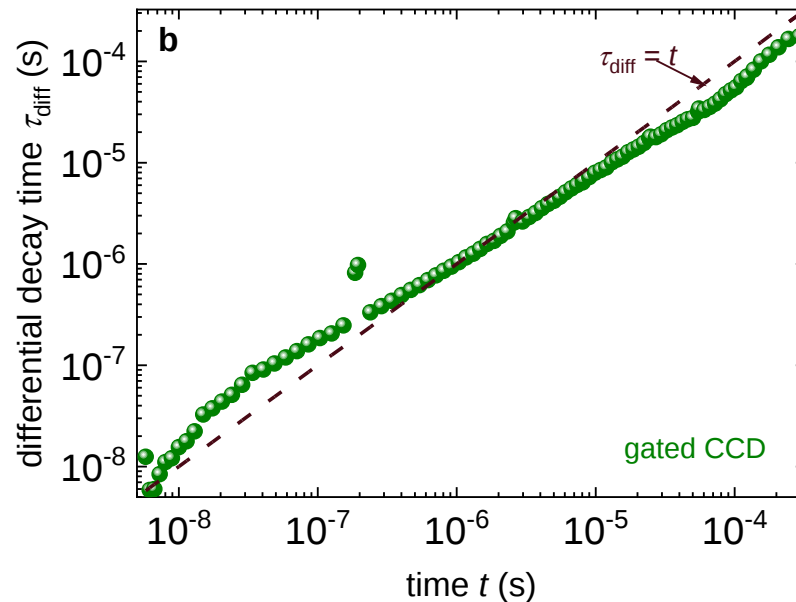
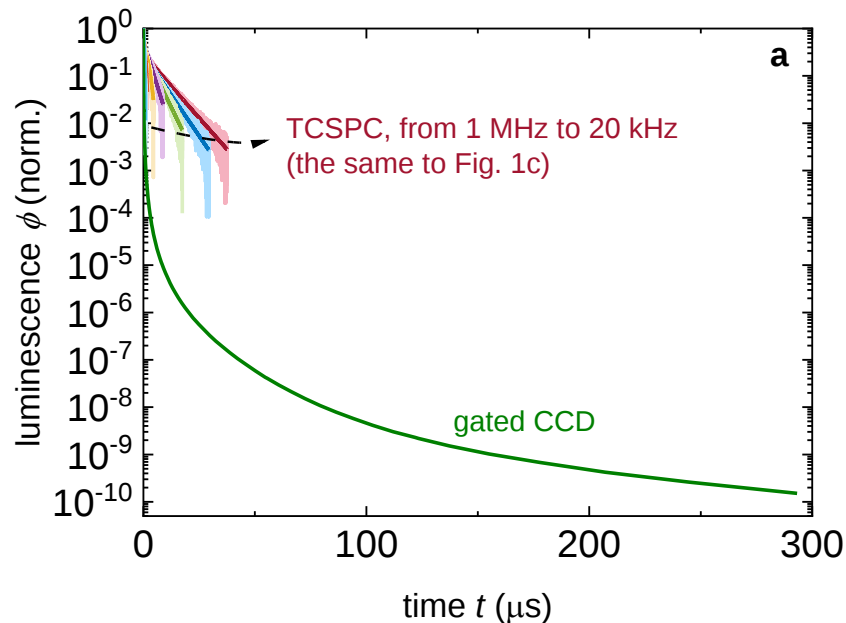


$$\frac{dn(t)}{dt} = -kn^2$$

$$\tau_{\text{diff}} = (kn(t))^{-1}$$

$$n(t) = \frac{n(0)}{1 + n(0)kt} \approx 1/(kt)$$

Why $\tau = t$ can be a decent approximation



$$\frac{dn(t)}{dt} = -kn^2$$

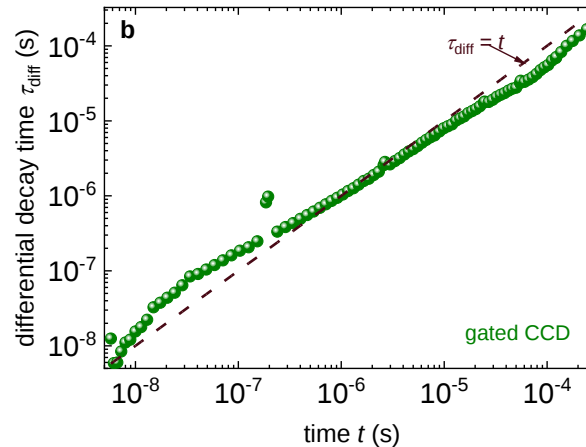
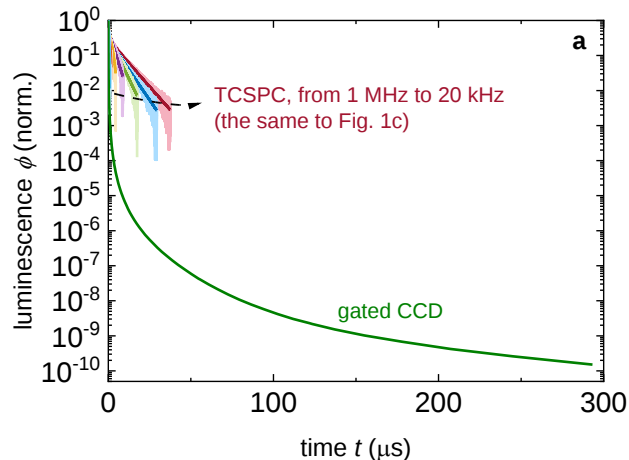
$$\tau_{\text{diff}} = (kn(t))^{-1}$$

$$n(t) = \frac{n(0)}{1 + n(0)kt} \approx 1/(kt)$$

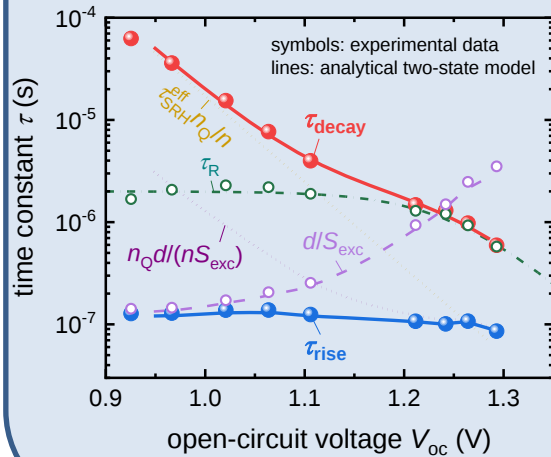
$$\tau_{\text{diff}} = t$$

If a sample is intrinsic, the following holds:

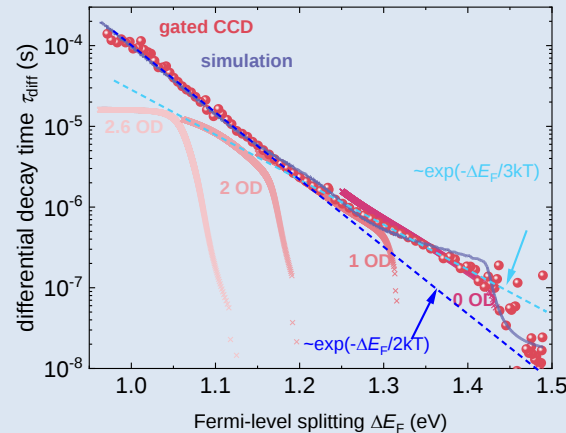
- Every decay not dominated by a deep defect will lead to non-exponential decays.
- Those are often similar to radiative recombination (even if they are not)
- They will automatically lead to $\tau_{\text{diff}} \approx t$ implying that decay times determined towards the end of a decay are $\sim$ the inverse repetition rate.



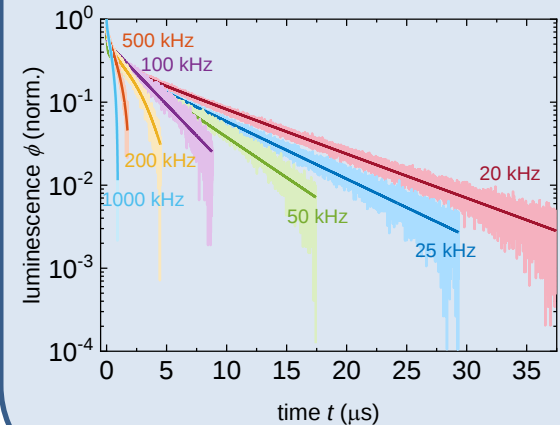
1) Rise and decay times $\rightarrow$ recombination and extraction times



2) Lifetime loses meaning. Effective k might be more useful.



3) $\tau \sim 1/f_{rep}$ is a risk to consider.

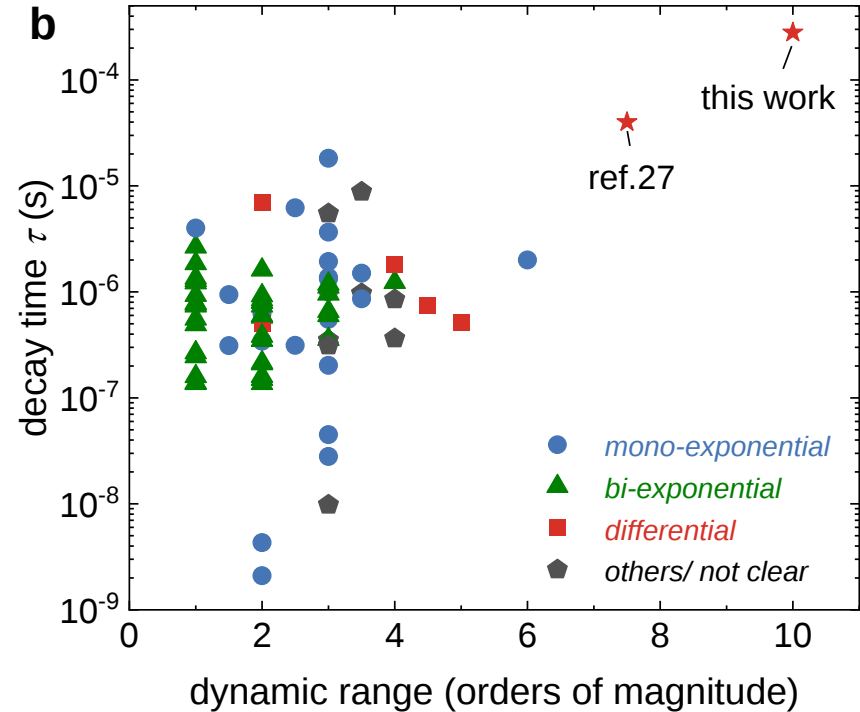
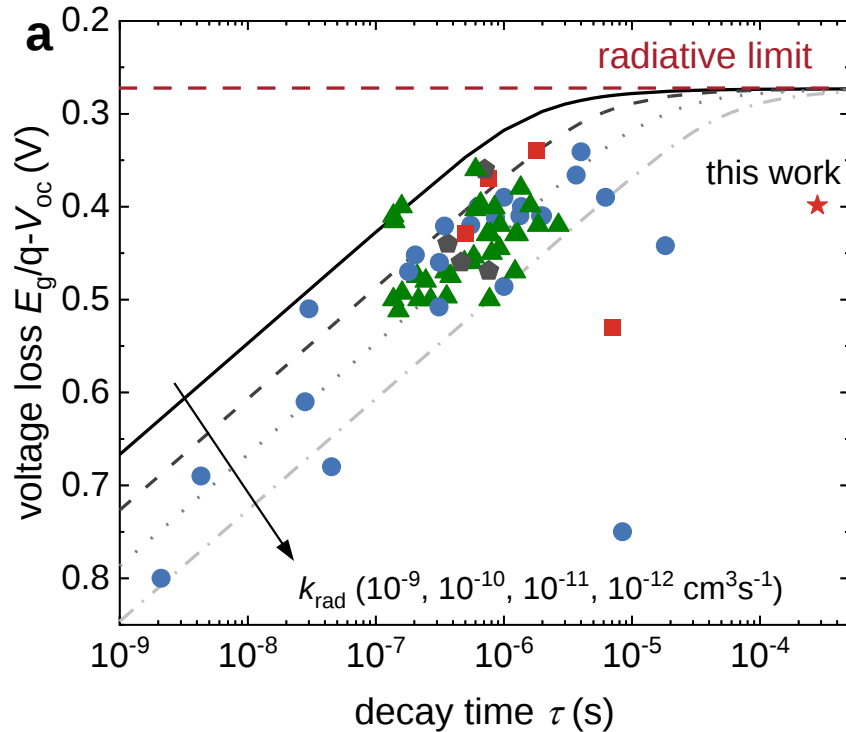




Funding from
Helmholtz Association
DFG
OCPC Fellowships

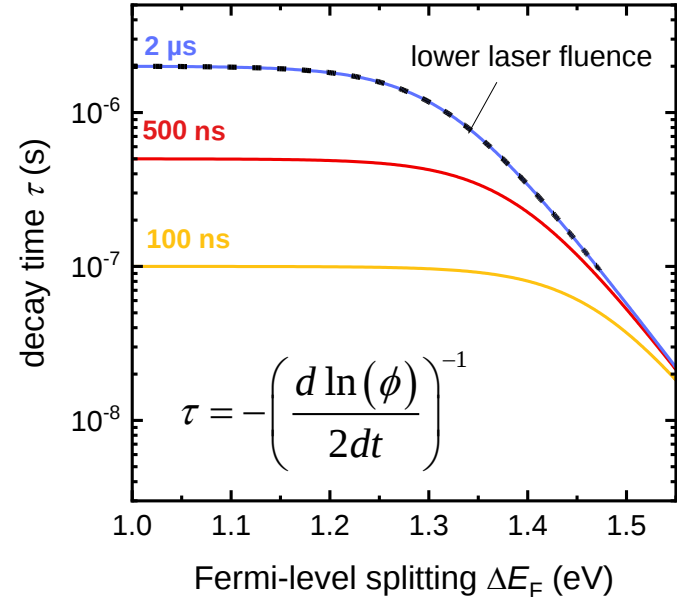
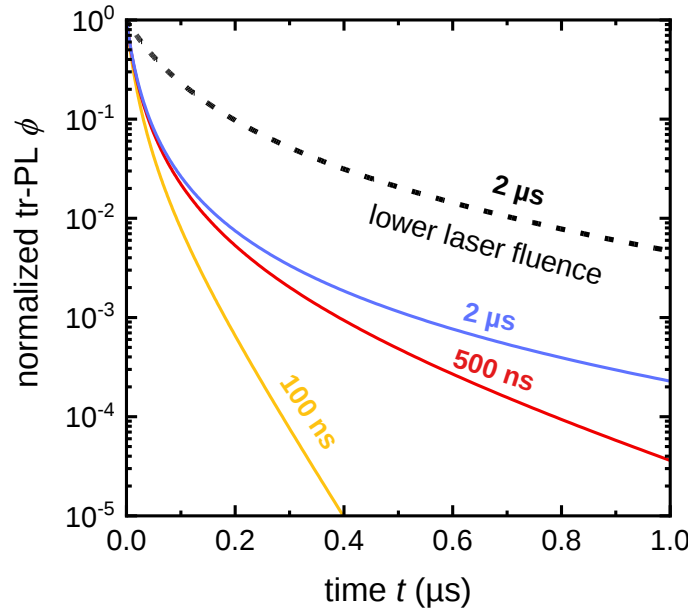
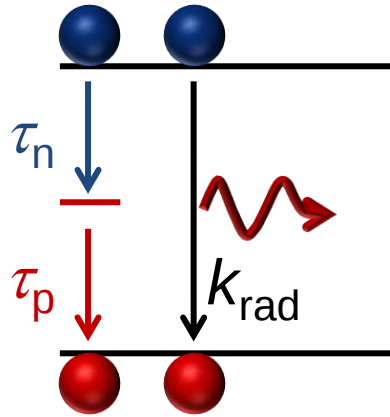
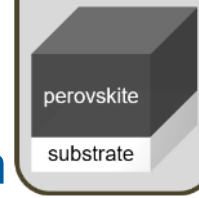
Thank you for your attention

The importance of dynamic range



Transient Photoluminescence

Layer on Glass – Bulk Recombination



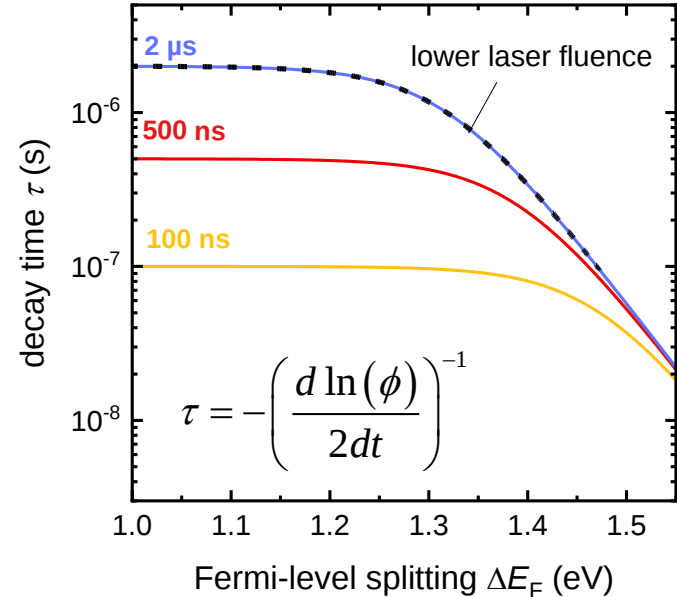
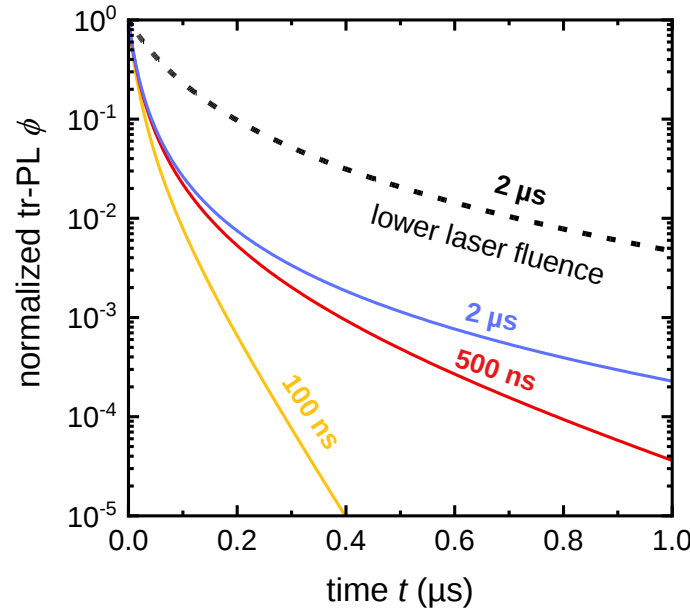
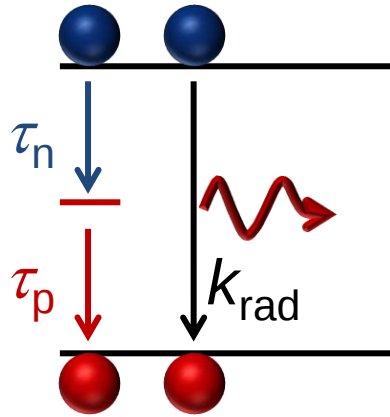
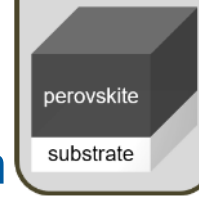
$$\frac{dn}{dt} = -k_{\text{rad}} n^2 - \frac{n}{\tau_p + \tau_n}$$

SRH + radiative recombination

← time

Transient Photoluminescence

Layer on Glass – Bulk Recombination



$$\tau_{\text{diff}} = -\frac{n}{dn/dt} = \frac{1}{k_{\text{rad}} n + \tau_p + \tau_n}$$

Decay Time

← time